Shanghai Fudan Microelectronics Group Company Limited



# **FM24N32** Wide Voltage Range 2-Wire Serial EEPROM

**Data Sheet** 

Oct. 2023



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## Description

The FM24N32 provides 32,768 bits of serial electrically erasable and programmable read-only memory (EEPROM) organized as 4,096 words of 8 bits each, with 128-bit UID and 32-byte Security Sector. The device's cascadable feature allows up to 8 devices to share a common 2-wire bus. The device is optimized for use in many industrial and commercial applications where ultra-low power and ultra-low voltage operations are essential.

### Features

- Low Operation Voltage: V<sub>cc</sub> = 1.7V to 5.5V
- Internally Organized: 4,096 x 8
- 2-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bi-directional Data Transfer Protocol
- 400Khz and 1MHz Clock Compatibility
- Support Software Data Protection (SWP)
- Support Configurable Device Address (CDA)
- 32-Byte Page Write Modes (Partial Page Writes are Allowed)
- Lockable 32-Byte Security Sector
- 128-Bit Unique ID for each device
- Operating Temperature – -40°C to +85°C
- Self-timed Write Cycle (5 ms max)
- High-reliability
  - Endurance: 4,000,000 Write Cycles
  - Data Retention: 100 Years
- SOP8, TSSOP8, USON8 and Thin 4-ball WLCSP Packages (RoHS Compliant and Halogen-free)

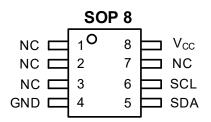
## **Absolute Maximum Ratings**

Ambient Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C
Voltage on Any Pin with Respect to Ground	-0.5V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0 mA

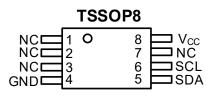
\*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

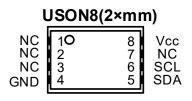
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## Packaging Type



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Note:

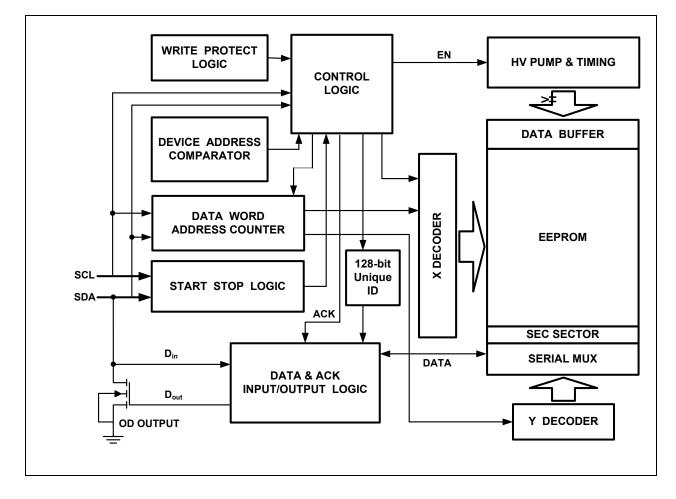
1. Please contact local sales office for detail description.

## **Pin Configurations**

Pin Name	Function
SDA	Serial Data Input/Output
SCL	Serial Clock Input
Vcc	Power Supply
GND	Ground
NC	Not Connect



### Figure 1. Block Diagram



## **Pin Description**

**SERIAL CLOCK (SCL):** The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

**SERIAL DATA (SDA):** The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

## Write Protect Description

If precautions are not taken, inadvertent writes may occur during transitions of the host system. The FM24N32 has provided SWP feature that will protect the memory against inadvertent writes. When SWP enabled, the whole memory will be read-only except SWP NVM bit. The SWP feature may be enabled (SWP=1'b) or disabled (SWP=0'b) by the user. The FM24N32 is shipped from FMSH with SWP disabled.

SWP Status	Part of the Memory Protected
SWP=1'b	Full Memory Protected
SWP=0'b	No Protected



### **Memory Organization**

**FM24N32, 32K SERIAL EEPROM:** Internally organized with 128 pages of 32 bytes each, the 32K requires a 13-bit data word address for random word addressing.

**Security Sector:** The FM24N32 offers 32-byte Security Sectors which can be written and (later) permanently locked in Read-only mode. This memory may be used by the system manufacturers to store security and other important information separately from the main memory array.

**Unique ID:** The FM24N32 utilizes a separate memory block containing a factory programmed read-only 128-bit unique ID.

**Configurable Device Address (CDA):** The FM24N32 provides the CDA features to allow as many as eight devices on the same bus. When power-on, the device will load the device address Configurations automatically. The CDA contains C0/C1/C2/CX four NVM bits. When CX is set to '1b', the device responds to all device address. Otherwise, the device only responds to the same device address as how C2/C1/C0 is set. The CDA factory default value is '0000b'.

**WREN**:FM24N32 offers a volatile register to protect CDA and SWP bit from unexpected write operation. Before writing CDA and SWP bit, the 'WREN' register must be previously set to 1'b. Because the register will be automatically set to 0'b after any read or write operation, the following command must be a 'Write CDA' command. The default value of 'WREN' register after power-on is 0'b.

Device ADDR	Page ADDR		Byte Number					
Device ADDR	Page ADDR	31	0					
	0							
	1							
1010	2		Data Memory (128P X 32B)					
	127							
1011	xxxx x00x	Security Sector (1P X 32B)						
1011	XXXX XXXX <sup>1</sup>							
1011	xxxx x01x		128 Bits Unique ID(UID)					
	XXXX XXXX <sup>2</sup>							
1011	xxxx x10x		1 Bit Lock Bit (LB)					
	XXXX XXXX <sup>3</sup>							
1011	xxxx 0110	Configurable Device Address (CDA) & SWP						
	1100 1010 <sup>4</sup>							
1011	xxxx 1111	WREN						
	0011 0101 <sup>5</sup>							

 Table 1. Memory Organization

Note: 1. Address bits ADDR<10:9> must be 00'b, ADDR<4:0> define byte address, other bits are don't care.

2. Address bits ADDR<10:9> must be 01'b, ADDR<3:0> define byte address, other bits are don't care.

3. Address bits ADDR<10:9> must be 10'b, other bits are don't care.

4. Address bits ADDR<11:0> must be 0, 0110, 1100, 1010'b, other bits are don't care.

5. Address bits ADDR<11:0> must be 1, 1111, 0011, 0101'b, other bits are don't care.

### Pin Capacitance

SYMBOL	PARAMETER	CONDITIONS	Мах	Units
C <sub>IN</sub> <sup>1</sup>	Input Capacitance	$V_{IN} = 0V, f = 1MHz$	6	pF
C <sub>OUT</sub> <sup>1</sup>	Output Capacitance	$V_{OUT} = 0V, f = 1MHz$	8	pF

Note: 1. This parameter is characterized and is not 100% tested.



## **Reliability Performance**

PA	RAMETER	SYMBOL	Test Condition	Max	Units
	ycle endurance age Mode)	Ncycle	$T_A = 25 \text{ °C}, V_{CC(min)} < V_{CC} < V_{CC(max)}$	4,000,000	Write cycle
Dat	a Retention	DR	T <sub>A</sub> = 55 °C	100	Year

#### Note:

1. This parameter is characterized and qualification. It is not 100% tested.

### **DC Characteristics**

Applicable over recommended operating range from:  $T_A$ = -40°C to +85°C,  $V_{CC}$ = +1.7V to +5.5V, (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Max	Units
V <sub>CC</sub>	Supply Voltage		1.7	5.5	V
Icc1	Supply Current	V <sub>CC</sub> =1.7V, Read at 400KHz		0.4	mA
I <sub>CC2</sub>	Supply Current	V <sub>CC</sub> =5.5V, Read at 400KHz		0.6	mA
I <sub>CC3</sub>	Supply Current	V <sub>CC</sub> = 1.7V, Write at 400KHz		0.7	mA
I <sub>CC4</sub>	Supply Current	V <sub>CC</sub> = 5.5V, Write at 400KHz		0.8	mA
I <sub>SB1</sub>	Standby Current	$V_{CC}$ =1.7V, $V_{IN}$ = $V_{CC}$ /GND		1.0	μA
I <sub>SB2</sub>	Standby Current	$V_{CC}$ = 5.5V, $V_{IN}$ = $V_{CC}$ /GND		5.0	μA
ILI	Input Leakage Current	V <sub>IN</sub> =V <sub>CC</sub> / GND		1.0	μA
ILO	Output Leakage Current	V <sub>OUT</sub> =V <sub>CC</sub> / GND		1.0	μA
V <sub>IL</sub> <sup>1</sup>	Input Low Level		-0.5	$V_{CC} x \ 0.3$	V
V <sub>IH</sub> <sup>1</sup>	Input High Level		V <sub>CC</sub> x 0.7	V <sub>CC</sub> +0.5	V
V <sub>OL2</sub>	Output Low Level 2	V <sub>CC</sub> = 3.0V, I <sub>OL</sub> =2.1 mA		0.4	V
V <sub>OL1</sub>	Output Low Level 1	$V_{CC}$ =1.7V, $I_{OL}$ = 0.15 mA		0.2	V

Note: 1.  $V_{IL}$  min and  $V_{IH}$  max are reference only and are not tested.

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## **AC Characteristics**

#### 400 kHz AC characteristics

Recommended operating conditions:  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +1.7V$  to +5.5V, CL = 100 pF (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	Min	Max	Units
<b>f</b> <sub>SCL</sub>	Clock Frequency, SCL		400	kHz
t <sub>LOW</sub>	Clock Pulse Width Low	1.3		μs
t <sub>HIGH</sub>	Clock Pulse Width High	0.6		μs
tı1	Noise Suppression Time		80	ns
t <sub>AA</sub>	Clock Low to Data Out Valid	0.1	0.9	μs
t <sub>BUF</sub> 1	Time the bus must be free before a new transmission can Start	1.3		μs
t <sub>HD.STA</sub>	Start Hold Time	0.6		μs
t <sub>su.sta</sub>	Start Setup Time	0.6		μs
t <sub>HD.DAT</sub>	Data In Hold Time	0		μs
t <sub>su.dat</sub>	Data In Setup Time	100		ns
t <sub>R</sub>	Inputs Rise Time <sup>1</sup>		300	ns
t⊦	Inputs Fall Time <sup>1</sup>		300	ns
t <sub>su.sто</sub>	Stop Setup Time	0.6		μs
t <sub>DH</sub>	Data Out Hold Time	100		ns
t <sub>WR</sub>	Write Cycle Time		5	ms

#### **1 MHz AC characteristics**

Recommended operating conditions:  $T_A = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +1.7V$  to +5.5V, CL = 100 pF (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	Min	Max	Units
f <sub>SCL</sub>	Clock Frequency, SCL		1	MHz
t <sub>LOW</sub>	Clock Pulse Width Low	500		ns
t <sub>HIGH</sub>	Clock Pulse Width High	300		ns
tı1	Noise Suppression Time		80	ns
t <sub>AA</sub>	Clock Low to Data Out Valid	100	450	ns
t <sub>BUF</sub> ¹	Time the bus must be free before a new transmission can Start	500		ns
t <sub>HD.STA</sub>	Start Hold Time	250		ns
t <sub>su.sta</sub>	Start Setup Time	250		ns
t <sub>HD.DAT</sub>	Data In Hold Time	0		ns
t <sub>su.dat</sub>	Data In Setup Time	50		ns
t <sub>R</sub>	Inputs Rise Time <sup>1</sup>		120	ns
t⊨	Inputs Fall Time <sup>1</sup>		120	ns
t <sub>su.sto</sub>	Stop Setup Time	250		ns
t <sub>DH</sub>	Data Out Hold Time	100		ns
t <sub>WR</sub>	Write Cycle Time		5	ms

**Notes:** 1. This parameter is characterized and is not 100% tested.

2. AC measurement conditions: RL (connects to V<sub>CC</sub>):  $1.3 \text{ k}\Omega$ Input pulse voltages:  $0.3 \text{ V}_{CC}$  to  $0.7 \text{ V}_{CC}$ Input and output timing reference voltages:  $0.5 \text{ V}_{CC}$ Input rise and fall times:  $\leq 50 \text{ ns}$ 



## **Device Operation**

**CLOCK and DATA TRANSITIONS:** The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (refer to Figure 4). Data changes during SCL high periods will indicate a start or stop condition as defined below.

**START CONDITION:** A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (refer to Figure 5).

**STOP CONDITION:** A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (refer to Figure 5).

**ACKNOWLEDGE:** All address and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

**STANDBY MODE:** The FM24N32 features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the stop bit and the completion of any internal operations.

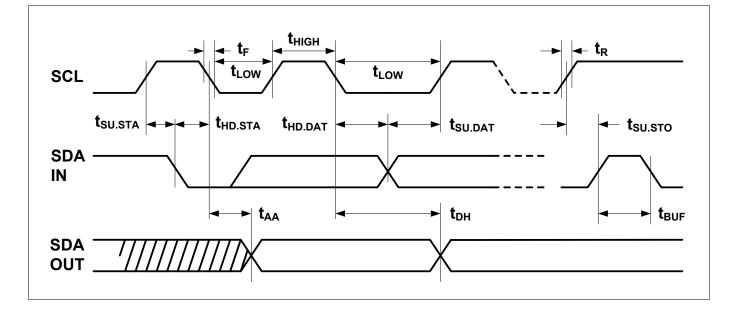
**Memory RESET:** After an interruption in protocol, power loss or system reset, any 2-wire part can be reset in following these steps:

1. Clock up to 9 Cycles,

- 2. Look for SDA high in each cycle while SCL is high and then,
- 3. Create a start condition as SDA is high.

### **Bus Timing**

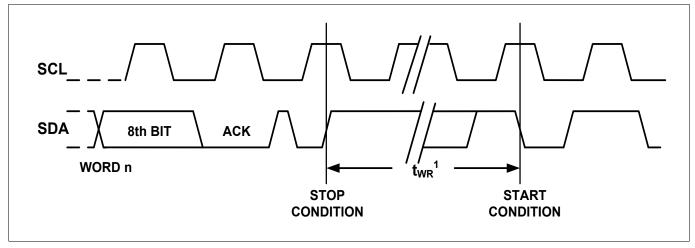






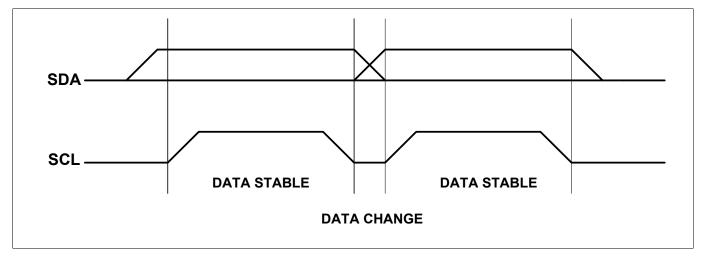
## Write Cycle Timing

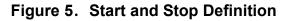


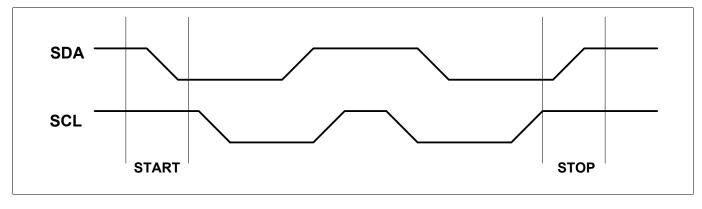


Note: 1. The write cycle time t<sub>WR</sub> is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

### Figure 4. Data Validity

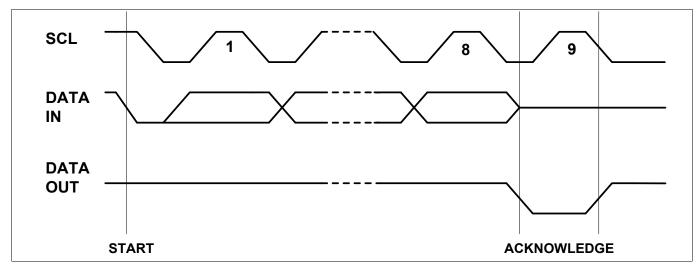






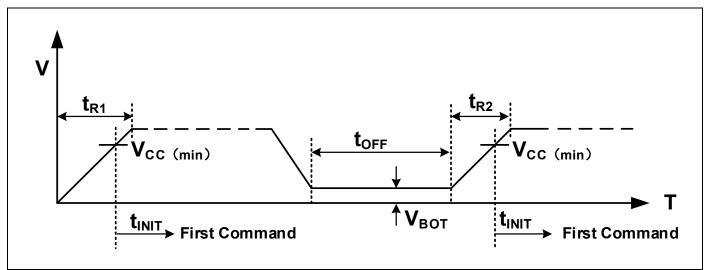


### Figure 6. Output Acknowledge



## **Power-up Timing**





Symbol	Parameter	Test Condition	Min	Max	Units
t <sub>R1</sub>	Power on time from 0V			20	ms
t <sub>R2</sub>	Power on time from $V_{\text{BOT}}$	V <sub>BOT</sub> ≪0.2V		5	ms
t <sub>OFF</sub>	power cycle off time		50		ms
<b>t</b> INIT	Time from power on to first command		100		us
<b>V</b> BOT	Power Off threshold for the next power on cycle	No ringback above $V_{BOT}$		0.2	V

Note: VCC must rise monotonically without ringback.

## **Device Addressing**

**Data Memory Access:** The 32K EEPROM device requires an 8-bit device address word following a start condition to enable the chip for a read or write operation (refer to Table 2~Table 4).

The device address word consists of a mandatory '1010' (Ah) sequence for the first four most significant bits as shown in Table 2. This is common to all the EEPROM devices.

The FM24N32 provides the Configurable Device Address (CDA) feature. When CX is set to '0b', the 32K EEPROM uses the three device address bits C2, C1, C0 to allow as many as eight devices on the same bus. These bits must compare to C2/C1/C0 bits in Configurable Device Address, refer to 'Memory Organization'. When CX is set to '1b', the device responds to any device address, thus only one device is allowed on each bus.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the device will return to a standby state.

**Unique ID Access:** The FM24N32 utilizes a separate memory block containing a factory programmed 128-bit unique ID. Access to this memory location is obtained by beginning the device address word with a '1011'(Bh) sequence (refer to Table 2). The behavior of the next three bits (C2/C1/C0) remains the same as during a standard memory addressing sequence.

The eighth bit of the device address needs be set to a one to read the Serial Number. Writing or altering the 128-bit unique ID is not possible.

For more details on accessing this special feature, See Read Operations on page 15.

**Security Sector Access:** The FM24N32 offers 32-byte Security Sector which can be written and (later) permanently locked in Read-only mode. Access to this memory location is obtained by beginning the device address word with a '1011' (Bh) sequence (refer to Table 2). The behavior of the next three bits (C2/C1/C0) remains the same as during a standard memory addressing sequence.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

For more details on accessing this special feature, See Write Operations and Read Operations on page 13-15.

**CDA and SWP Access:** Access to this memory location is obtained by beginning the device address word with a '1011b' (Bh) sequence (refer to Table 2). The behavior of the next three bits (C2/C1/C0) remains the same as during a standard memory addressing sequence.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

For more details on accessing this special feature, See Write Operations and Read Operations on page 13-15.

**NOISE PROTECTION:** Special internal circuitry placed on the SDA and SCL pins prevent small noise spikes from activating the device.

**DATA SECURITY:** FM24N32 has provided SWP feature that will protect the memory against inadvertent writes. When SWP enabled, the whole memory will be read-only except SWP NVM bit. The SWP feature may be enabled (SWP=1'b) or disabled (SWP=0'b) by the user. The FM24N32 is shipped from FMSH with SWP disabled.

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### Table 2. Device Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	1	0	1	0	C2	C1	C0	R/W
Security Sector	1	0	1	1	C2	C1	C0	R/W
Security Sector Lock Bit	1	0	1	1	C2	C1	C0	R/W
Unique ID Number	1	0	1	1	C2	C1	C0	1
CDA and SWP	1	0	1	1	C2	C1	C0	R/W
WREN	1	0	1	1	C2	C1	C0	0
	MSB							LSB

### Table 3. First Word Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	х	х	х	х	A11	A10	A9	A8
Security Sector	х	х	х	х	х	0	0	х
Security Sector Lock Bit	х	х	х	х	х	1	0	Х
Unique ID Number	х	х	х	х	х	0	1	х
CDA and SWP	х	х	х	х	0	1	1	0
WREN	х	х	х	х	1	1	1	1
MSB								LSB

NOTE: x = Don`t care bit.

#### Table 4. Second Word Address

Access Area	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
Data Memory	A7	A6	A5	A4	A3	A2	A1	A0
Security Sector	х	х	A5	A4	A3	A2	A1	A0
Security Sector Lock Bit	х	х	х	х	х	х	х	х
Unique ID Number	х	х	х	х	0	0	0	0
CDA and SWP	1	1	0	0	1	0	1	0
WREN	0	0	1	1	0	1	0	1
	MSB							LSB

NOTE: x = Don`t care bit.



**BYTE WRITE:** A write operation requires two 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally-timed write cycle, t<sub>WR</sub> to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 8).

**PAGE WRITE:** The 32K EEPROM is capable of 32-byte page writes. A page write is initiated the same way as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 31 more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 9).

The data word address lower seven bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 32 data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

**ACKNOWLEDGE POLLING:** Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the read or write sequence to continue.

**WRITE SECURITY SECTOR:** Write the Security Sector is similar to the page write but requires use of device address, and the special word address seen in Table 2-Table 4 on page 12. The higher address bits ADDR<15:5> are don't care except for address bits ADDR<10:9>, which must be equal to '00b'. Lower address bits ADDR<4:0> define the byte address inside the Security Sector (see Figure 13).

If the Security Sector is locked, the data bytes transferred during the Write Security Sector operation are not acknowledged (NoAck).

**LOCK SECURITY SECTOR:** Lock the Security Sector is similar to the byte write but requires use of device address, and special word address seen in Table 2-Table 4 on page 12. The word address bits ADDR<10:9> must be '10b', all other word address bits are don't care. The data byte must be equal to the binary value xxxx xx1x, where x is don't care (see Figure 15).

If the Security Sector is locked, the data bytes transferred during the Lock Security Sector operation are not acknowledged (NoAck).

#### WREN:

The FM24N32 offers a volatile register to protect CDA & SWP bit from unexpected write operation. Before writing CDA and SWP, the 'WREN' register must be previously set to 1. Because the register will be automatically set to 0 after any read or write operation, the following command must be a 'Write CDA' command. The default value of 'WREN' register after power-on is 0b.

Write the 'WREN' register is similar to the page write but requires use of device address, and the special word address seen in Table 2-Table 4 on page 12. The word address bits ADDR<11:0> must be '1111, 0011, 0101b', and ADDR<15:12> is don't care. After the word address bytes, the register will be set and will be cleared after next command. That is, a following WRITE CDA and SWP command should be performed. For 'WREN' is a volatile register, no write cycle time is needed in this command (see Figure 18).

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**WRITE CDA & SWP:** Before writing CDA & SWP, a previously 'WREN' command must be performed. Write CDA & SWP operation is similar to the byte write but requires use of device address, and specific word address. The word address bits ADDR<11:0> must be '0110, 1100, 1010b' (see Table 3-Table 4), and ADDR<15:12> is don't care. The data byte must be equal to the binary value 'C2C1C0CXxxSWPx' (see Table 5 and Figure 19).

CDA and SWP NVM Bit defined as following Table 5:

#### Table 5. CDA and SWP NVM Bit

Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0
C2	C1	C0	CX	х	х	SWP	х
MSB							LSB

NOTE: x = Don`t care bit.

Refer to ordering information on page 21 for the CDA factory default value. The SWP bit default value is '0b' (SWP disabled). CDA could be configured when SWP is disabled. If SWP is disabled, CDA and SWP could be re-configured in the same write operations. Once CDA re-configured, the following command with device address bits must be in accordance with the modified CDA, otherwise the device will return to standby state. If SWP is enabled, CDA is protected by SWP. CDA can't be modified even during the SWP disable operation, the value of CDA (C2'/C1'/C0'/ CX') in DATA0 of write CDA & SWP command sequence is ignored.

#### Note:

- 1. The CDA status could be checked by Ack polling. There will be an Ack when C2C1C0 value in device addresses of command sequence is correct according to CDA, otherwise NoAck.
- Write CDA & SWP operation do not support Ack polling to check whether the internal write cycle has completed. The next instruction issuing must wait for the end of the internal write cycle(t<sub>WR</sub>(max)=5ms), otherwise the instruction is invalid.



## **Read Operations**

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one.

**CURRENT ADDRESS READ:** The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (see Figure 10).

**RANDOM READ:** A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (see Figure 11).

**SEQUENTIAL READ:** Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 12).

**UNIQUE ID READ:** Reading the serial number is similar to the sequential read but requires use of the device address, a dummy write, and the use of specific word address seen in Table 2-Table 4 on page 12. The higher address bits ADDR<15:4> are don't care except for address bits ADDR<10:9>, which must be equal to '01b'. Lower address bits ADDR<3:0> define the byte address inside the UID. If the application desires to read the first byte of the UID, the lower address bits ADDR<3:0> would need to be '0000b'.

When the end of the 128-bit UID number is reached (16 bytes of data), the data word address will roll-over back to the beginning of the 128-bit UID number. The Unique ID Read operation is terminated when the microcontroller does not respond with a zero (ACK) and instead issues a Stop condition (see Figure 17).

**READ SECURITY SECTOR:** Read the Security Sector is similar to the random read but requires use of device address, a dummy write, and the use of specific word address seen in Table 2-Table 4 on page 12. The higher address bits ADDR<15:5> are don't care except for address bits ADDR<10:9>, which must be equal to '00b'. The lower address bits ADDR<4:0> define the byte address inside the Security Sector.

The internal byte address is automatically incremented to the next byte address after each byte of data is clocked out. When the last byte (1Fh) is reached, it will roll over to 00h, the first byte of the Security Sector, and continue to increment. (see Figure 14).

**READ LOCK STATUS:** There are two ways to check the lock status of the Security Sector.

1. The first way is initiated by a Security Sector Write, the EEPROM will acknowledge if the Security Sector is unlocked, while it will not acknowledge if the Security Sector is locked.

Once the acknowledge bit is read, it is recommended to generate a Start condition followed by a Stop condition, so that:

- Start: the truncated command is not executed because the Start condition resets the device internal logic
- Stop: the device is then set back into Standby mode by the Stop condition.

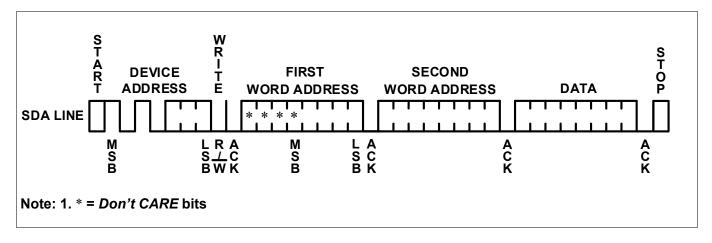
2. The second way is initiated by a Lock Status Read. Lock Status Read is similar to the random read but requires use of device address seen in Table 2-Table 4 on page 12, a dummy write, and the use of specific word address. The address bits ADDR<10:9> must be '10b', all other address bits are Don't Care. The Lock bit is the BIT1 of the byte read on SDA. It is at "1" when the lock is active and at "0" when the lock is not active. The same data is shifted 上海复旦微电子集团股份有限公司



out repeatedly until the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 16).

**READ CDA & SWP:** Read CDA & SWP operation is similar to the random read but requires use of device address, a dummy write, and specific word address. The word address bits ADDR<11:0> must be '0110, 1100, 1010b' (see Table 2-Table 4), and ADDR<15:12> is don't care. The CDA is the BIT7~BIT4 of the byte read on SDA, and SWP is the BIT1, other bits are don't care. The internal byte address is not automatically incremented, so the same data is shifted out repeatedly until the microcontroller does not respond with a zero but does generate a following stop condition (see Figure 20).

### Figure 8. Byte Write



### Figure 9. Page Write

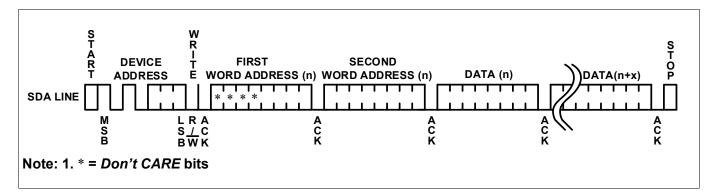
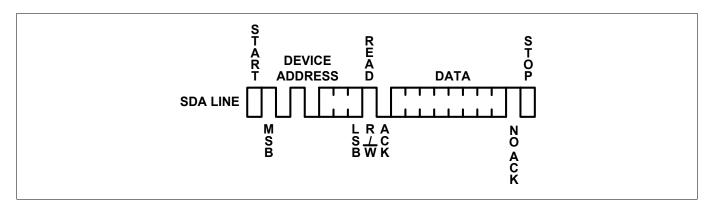


Figure 10. Current Address Read



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### Figure 11. Random Read

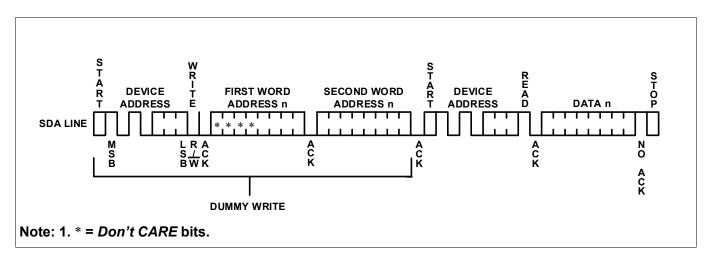


Figure 12. Sequential Read

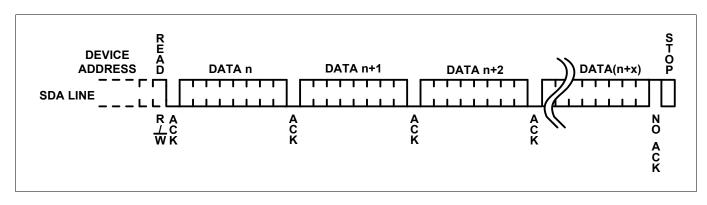
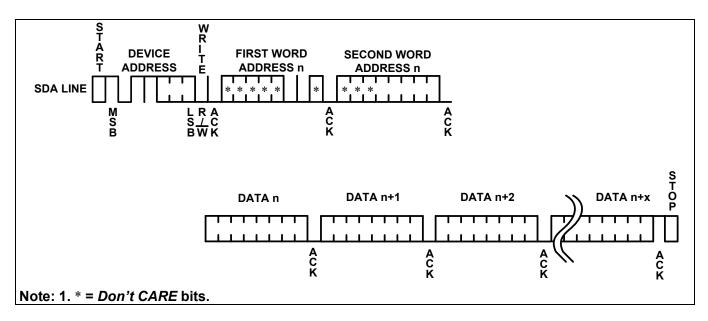
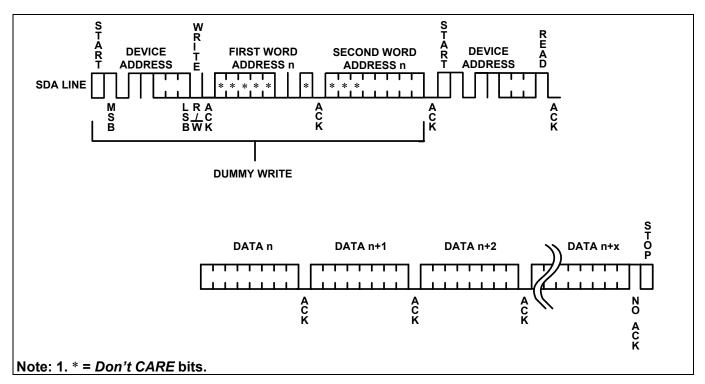


Figure 13. Write Security Sector

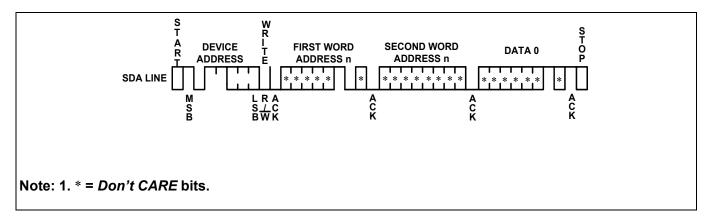








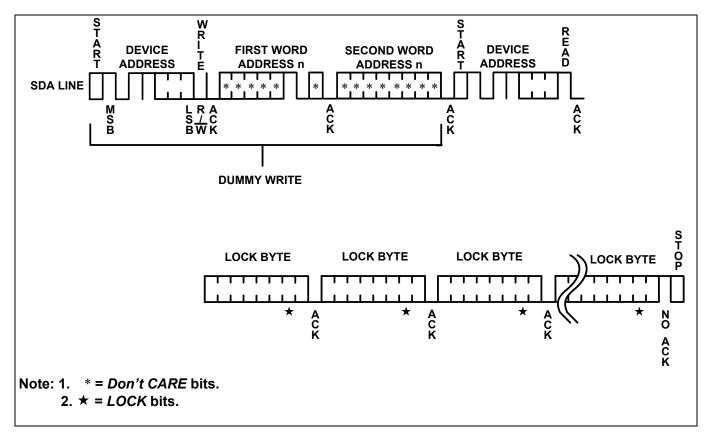
### Figure 15. Lock Security Sector



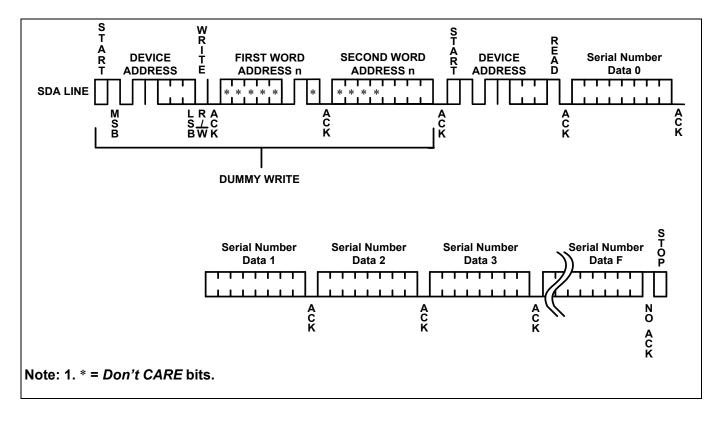
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### Figure 16. Read Lock Status

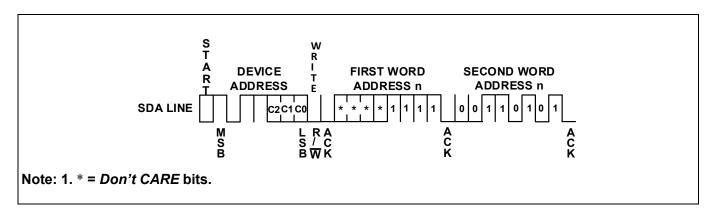


### Figure 17. Read Unique ID

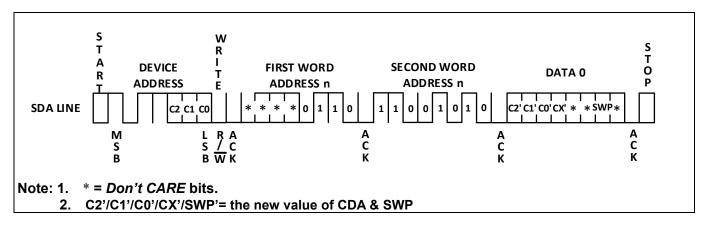




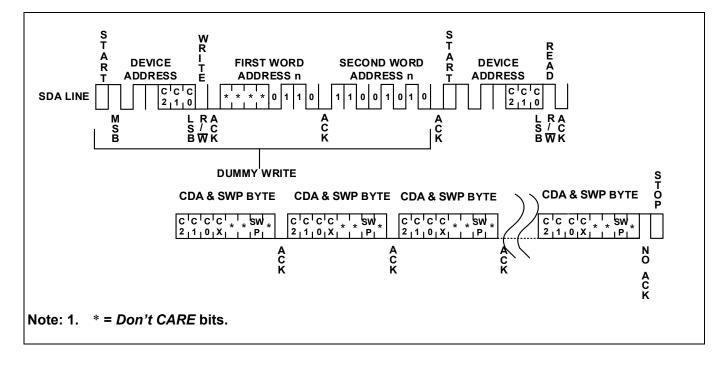
### Figure 18. WREN











## **Ordering Information**

	FM	24N	32	TX - PKG -T - GM - OP
Company Prefix	$\top$		Τ	$\top$ $\top$ $\top$ $\top$ $\top$ $\top$ $\top$
FM = Shanghai Fudan Microelectronics Group Co.,It	d			
Product Family				
24N = 2-Wire Serial EEPROM with 128-bit Unique ID with 32-byte Security Sector Supply voltage from 1.7V to 5.5V				
Product Density				
32 = 32K-bit				
Temperature Grade				
I3 = Industrial: -40 ℃~ +85 ℃				
Package Type <sup>(1)</sup>				
SO = 8-pin SOP TS = 8-pin TSSOP SN = 8-pin USON (2x3mm, 0.45mm thickness) CTE = 4-Ball Thin WLCSP, Ball pitch 400um x 400u	m			
Product Carrier				
U = Tube T = Tape(8mm) and Reel				
HSF ID Code				
G = RoHS Compliant, Halogen-free, Antimony-free				
MSL Level				
1 = MSL1 3 = MSL3				
OPTION <sup>(3)</sup>				

A0 = The CDA factory default value is '0000b'

A2 = The CDA factory default value is '0010b'

#### Note:

- 1. For SO package, MSL1 package are available, for detail please contact local sales office. For WLCSP package please contact local sales office.
- 2. For other configuration, please contact local sales office.

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## Part Marking Scheme

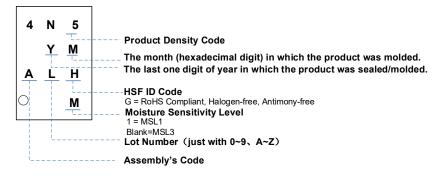
### SOP8

EMOANOOIO	
FM24N32I3	
YYWWALHM	
	<pre>Moisture Sensitivity Level 1 = MSL1</pre>
	Blank=MSL3
	HSF ID Code R = RoHS Compliant
	G = RoHS Compliant, Halogen-free, Antimony-free
	Lot Number(just with 0~9、A~Z)
	Assembly's Code
· · · · · · · · · · · · · · · · · · ·	Work week during which the product was molded (egweek 12)
l	The last two digits of the year In which the product was sealed/ molded.

### TSSOP8

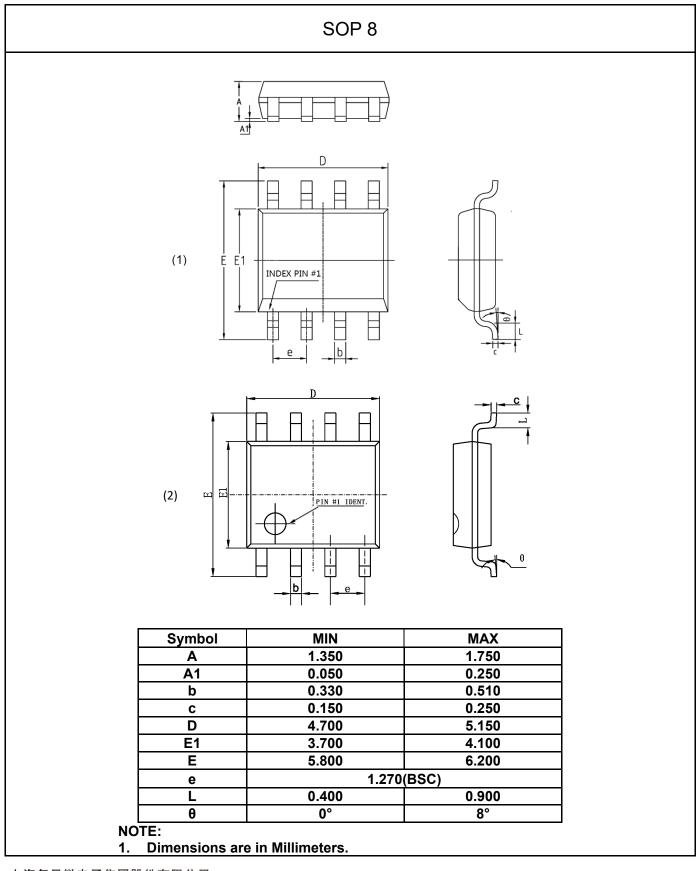
FM24N32I3	
YYWWALHM	
	Moisture Sensitivity Level 1=MSL1 Blank=MSL3
	R = RoHS Compliant
	G = RoHS Compliant, Halogen-free, Antimony-free
	Lot Number (just with 0~9、A~Z)
· · · · · · · · · · · · · · · · · · ·	Assembly's Code
	Work week during which the product was molded (egweek 12)
	The last two digits of the year In which the product was sealed / molded.

### **USON8**

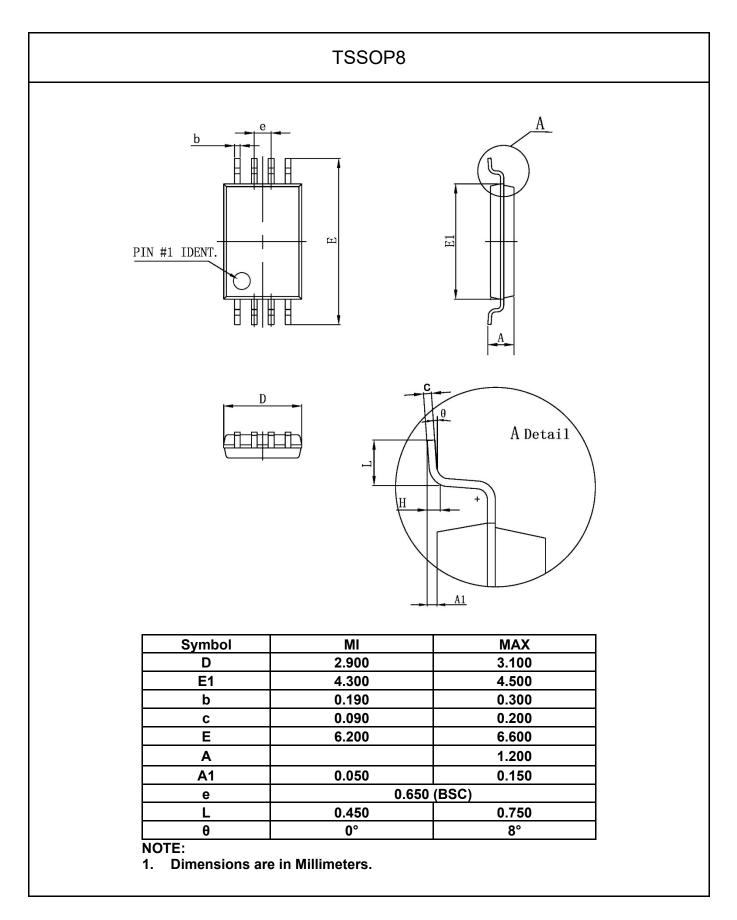




## **Packaging Information**

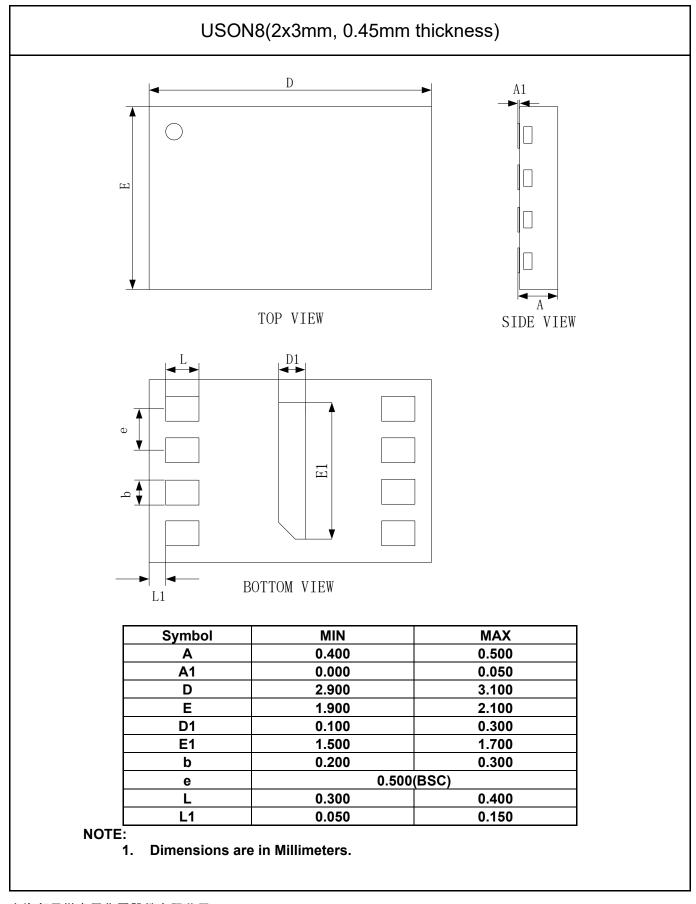






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## **Revision History**

Version	Publication date	Pages	Revise Description	
1.0	Oct. 2023	27	Initial document Release.	



### Sales and Service

Shanghai Fudan Microelectronics Group Co., Ltd. Address: Bldg No. 4, 127 Guotai Rd, Shanghai City China. Postcode: 200433 Tel: (86-021) 6565 5050 Fax: (86-021) 6565 9115

#### Shanghai Fudan Microelectronics (HK) Co., Ltd.

Address: Unit 506, 5/F., East Ocean Centre, 98 Granville Road, Tsimshatsui East, Kowloon, Hong Kong Tel: (852) 2116 3288 2116 3338 Fax: (852) 2116 0882

#### **Beijing Office**

Address: Room 423, Bldg B, Gehua Building, 1 QingLong Hutong, Dongzhimen Alley north Street, Dongcheng District, Beijing City, China. Postcode: 100007 Tel: (86-010) 8418 6608 Fax: (86-010) 8418 6211

#### Shenzhen Office

Address: Room.2306-2308, Building A7, Chuangzhi Cloud City, Liuxian Avenue, Xili Street, Nanshan District, Shenzhen, China. Postcode: 518000 Tel: (86-0755) 8335 0911 8335 1011 8335 2011 8335 0611 Fax: (86-0755) 8335 9011

# Shanghai Fudan Microelectronics (HK) Ltd Taiwan Representative Office

Address: Unit 1225, 12F., No 252, Sec.1 Neihu Rd., Neihu Dist., Taipei City 114, Taiwan Tel : (886-2) 7721 1889 Fax: (886-2) 7722 3888

# Shanghai Fudan Microelectronics (HK) Ltd Singapore Representative Office

Address : 47 Kallang Pudding Road, #08-06,The Crescent @ Kallang ,Singapore 349318 Tel : (65) 6443 0860 Fax: (65) 6443 1215

#### Fudan Microelectronics (USA) Inc.

Address : 97 E Brokaw Road, Suite 320,San Jose,CA 95112 Tel : (+1)408-335-6936

#### Web Site: http://www.fmsh.com/